Preliminary Data Sheet





TO-56 Packaged Laser Diode

High Power Single-Mode and Multi-Mode SemiNex Lasers 12xx to 19xx nm Custom Wavelengths Available Lensed Options Available

ApplicationsOEM Medical

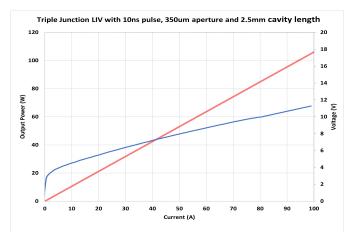
- Professional Medical
- LiDAR
- Military / AerospaceIllumination

Features

- Cost effective
- . High Output Power
- High Dynamic Range .
- High EfficiencyStandard Low Cost Package

SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary we will further optimize the design of our InP laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.





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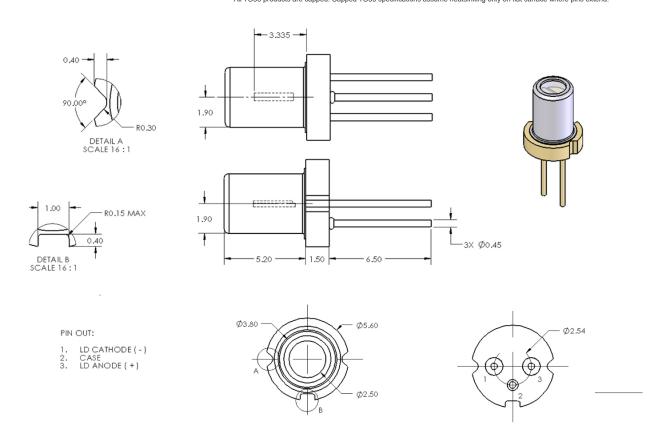
Triple Junction TO56





	Symbol	TO56-267	Units
Optical			
Wavelength	λ _c	1550	nm (±20)
Output Power (<10ns)	P。	100.00	watts (±10%)
Output Power (150ns)	P•	75.00	watts (±10%)
Cavity Length (typ.)	CL	2500	μm
No. of Junctions		3	
Emitter Width	W	350	μm
Emitter Height	Н	10	μm
Operating Current (<10ns)	I _{op}	100	A
Operating Current (150ns)	I _{op}	75	A
Operating Voltage	V _{op}	12	V
Threshold Current	Ith	2	A
Specifications			
Spectral Width	δλ	22	nm 3dB
Fast Axis Div.	Θ_perp	28	deg FWHM
Slow Axis Div.	O_parallel	12	deg FWHM
Pulse Width	PW	150	ns
Duty Cycle	DC	0.1	%
Mechanical			
Weight		0.5	g
Operating Temp.**		-40 to 85	°C
Storage Temp.		-40 to 85	°C

**Specified operating conditions are based on 20C heat sink temperature. High temperature operation will reduce performance and MTTF. Unless otherwise indicated all values are nominal. All TO56 products are capped. Capped TO56 specifications assume heatsinking only on flat surface where pins extend.



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DANGER LE / INVISIBLE LASER RADIAT CLASS IIIb and IV LASER PRODUCTS s product complies with 21CFR1040 as applicab er aperture is on the test station. Laser radiation this product is considered an auch Pazard to b This Lase from skin

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Date Created: Dec 1 2023 1:11PM UTC